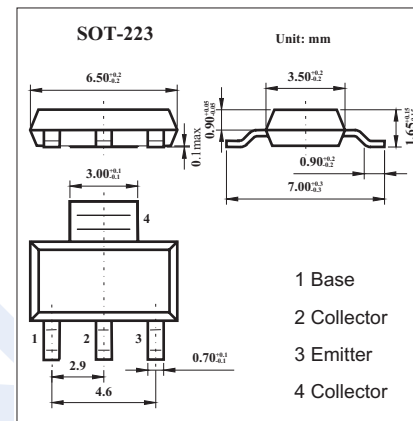


## Surface Mount PNP Silicon Power Darlington Transistor KZT127 (CZT127)

### ■ Features

- High current (max. 5A).
- Low voltage (max. 100V).



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-100	V
Collector-emitter voltage	V <sub>CEO</sub>	-100	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>c</sub>	-5	A
	I <sub>cP</sub>	-8	A
Base current	I <sub>B</sub>	-120	mA
power dissipation	P <sub>D</sub>	2	W
Thermal Resistance.Junction-to-Ambient	R <sub>θJA</sub>	62.5	°C/W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to emitter breakdown voltage	V <sub>CEO</sub>	I <sub>c</sub> =-30mA	-100			V
Collector cutoff current	I <sub>CEO</sub>	V <sub>CE</sub> =-50V			-500	μA
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = -100 V			-200	μA
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> = -5.0 V			-2.0	mA
DC current gain	h <sub>FE</sub>	I <sub>c</sub> = -500 mA; V <sub>CE</sub> = -3.0 V	1000			
		I <sub>c</sub> = -3A; V <sub>CE</sub> = -3.0V	1000			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = -3.0A; I <sub>B</sub> = -12mA			-2.0	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = -5.0A; I <sub>B</sub> = -20mA			-4.0	V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f=1.0MHz			300	pF
Transition frequency	f <sub>T</sub>	I <sub>c</sub> = -3A; V <sub>CE</sub> = -4V; f = 1.0 MHz	4.0			MHz